

Standard Rectifier

$$V_{RRM} = 1200V$$

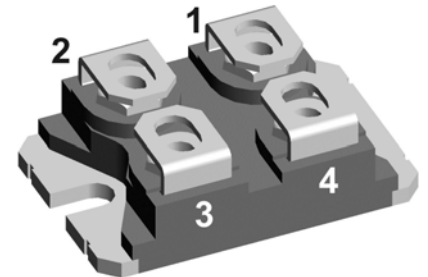
$$I_{FAV} = 2 \times 60A$$

$$V_F = 1.22V$$

Parallel legs

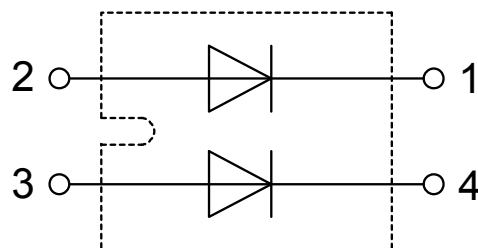
Part number

DSI2x55-12A



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

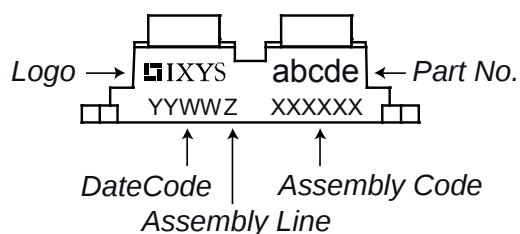
Package: SOT-227B (minibloc)

- Isolation Voltage: 3000V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 60\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.26	V
		$I_F = 120\text{ A}$				1.54	V
		$I_F = 60\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.22	V
		$I_F = 120\text{ A}$				1.58	V
I_{FAV}	average forward current	$T_C = 95^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			60	A
V_{FO}	threshold voltage	} for power loss calculation only				0.83	V
r_F	slope resistance					6.2	m Ω
R_{thJC}	thermal resistance junction to case					0.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				210	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			800	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			865	A
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			680	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			735	A
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			3.20	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			3.12	kA ² s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			2.31	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			2.25	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$			25		pF

Package SOT-227B (minibloc)				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal				150	A	
T _{stg}	storage temperature			-40		150	°C	
T _{vj}	virtual junction temperature			-40		150	°C	
Weight					30		g	
M _D	mounting torque			1.1		1.5	Nm	
M _T	terminal torque			1.1		1.5	Nm	
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm	
d _{Spb/Apb}		terminal to backside	8.6	6.8			mm	
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000			V
		t = 1 minute			2500			V

Product Marking



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSI2x55-12A	DSI2x55-12A	Tube	10	477052

Similar Part	Package	Voltage class
DSI2x55-16A	SOT-227B (minibloc)	1600

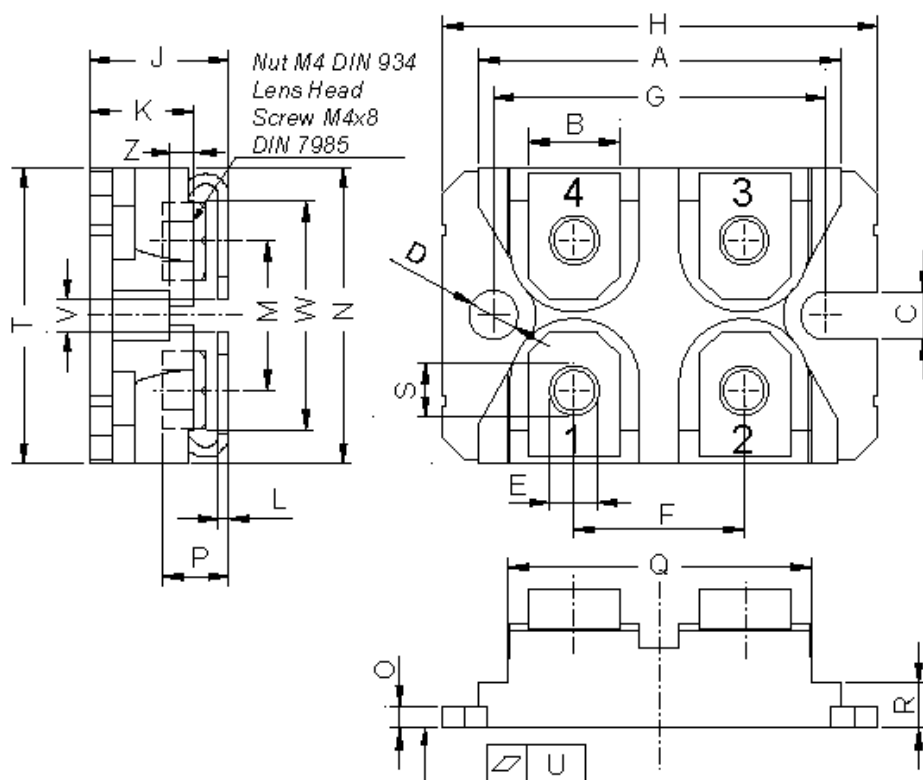
Equivalent Circuits for Simulation

* on die level

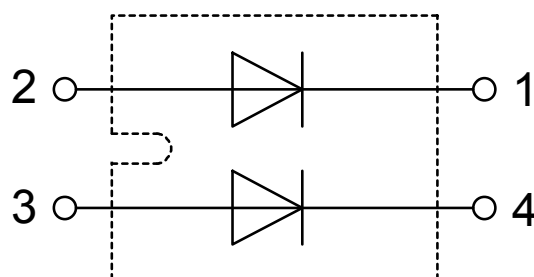
$T_{vj} = 150^\circ\text{C}$

		Rectifier	
$V_{0\max}$	threshold voltage	0.83	V
$R_{0\max}$	slope resistance *	4.3	mΩ

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



Rectifier

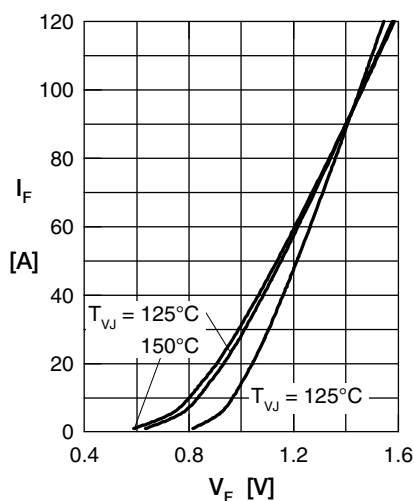


Fig. 1 Forward current versus voltage drop per diode

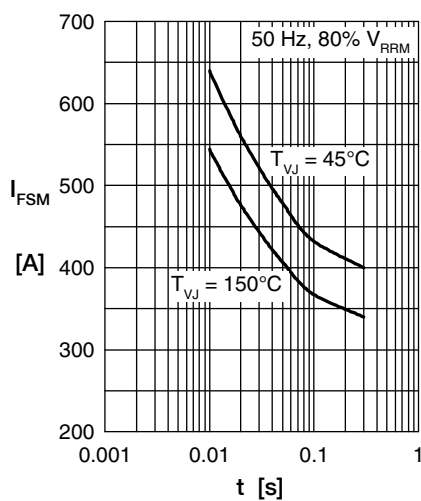


Fig. 2 Surge overload current

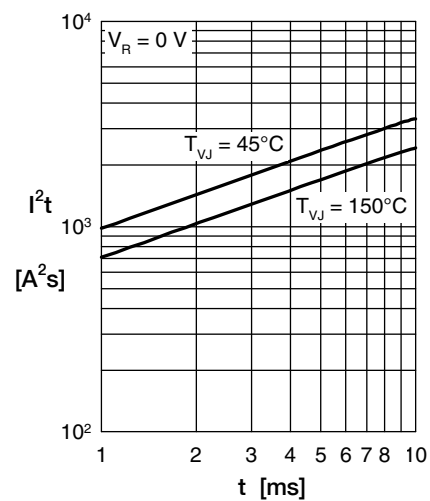


Fig. 3 I^2t versus time per diode

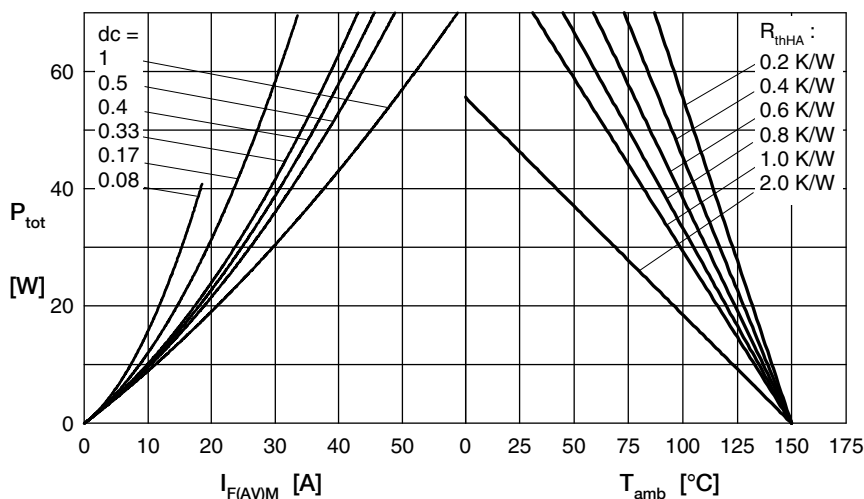


Fig. 4 Power dissipation vs. direct output current & ambient temperature

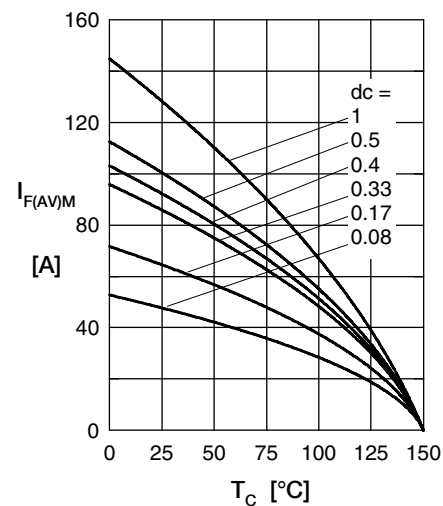


Fig. 5 Max. forward current versus case temperature

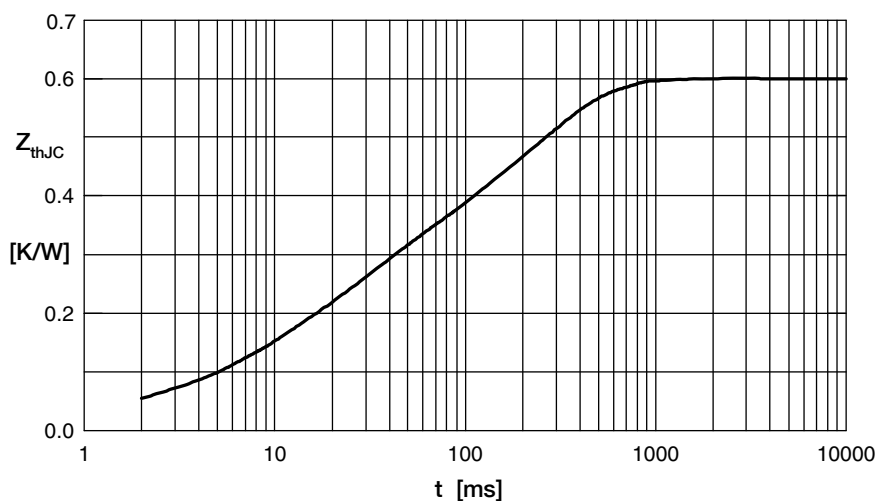


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.031	0.00024
2	0.0554	0.0036
3	0.114	0.0235
4	0.281	0.142
5	0.1686	0.7